STD127DT4



High voltage fast-switching NPN power transistor

Datasheet - production data

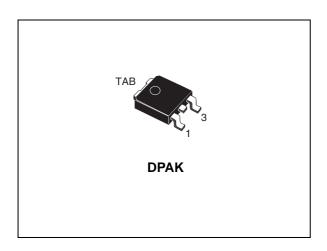
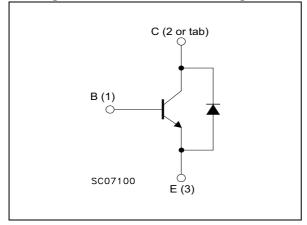


Figure 1. Internal schematic diagram



Features

- NPN transistor
- High voltage capability
- · Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed
- Integrated anti-parallel collector emitter diode

Applications

- Electronic ballast for fluorescent lighting
- Fly back and forward single transistor low power converters

Description

This device is manufactured using high voltage multi epitaxial planar technology for high switching speeds and medium voltage capability. It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA. The device is designed for use in lighting applications and low cost switch-mode power supplies.

Table 1. Device summary

Part number	Marking	Package	Packaging
STD127DT4	D127D	DPAK	Tape and reel

Contents STD127DT4

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STD127DT4 Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	700	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	400	V
V _{EBO}	Emitter-base voltage ($I_C = 0$; $I_B = 2$ A, $t_p < 10 \mu s$, $T_J = 150 °C$)	V _{(BR)EBO}	V
Ic	Collector current	4	Α
I _{CM}	Collector peak current (t _P < 5 ms)	8	Α
I _B	Base current	2	Α
I _{BM}	Base peak current (t _P < 5 ms)	4	Α
P _{tot}	Total dissipation at $T_c \le 25$ °C	35	W
T _{stg}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case max	3.57	°C/W
R _{thJA}	Thermal resistance junction-ambient max	100	°C/W

Electrical characteristics STD127DT4

2 Electrical characteristics

(T_{case} = 25°C unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (V _{BE} =0)	V _{CE} = 700 V			100	μΑ
I _{CEO}	Collector cut-off current (I _B =0)	V _{CE} = 400 V			250	μΑ
V _{(BR)EBO}	Emitter - base breakdown voltage $(I_C = 0)$	I _E =10 mA	9		18	V
V _{CEO(sus)} ⁽¹⁾	Collector-emitter sustaining voltage (I _B = 0)	I _C =100 mA	400			V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	$I_C = 1 \text{ A}$ $I_B = 0.2 \text{ A}$ $I_C = 4 \text{ A}$ $I_B = 1 \text{ A}$	`		0.3 1.3	V V
V _{BE(sat)} (1)	Base-emitter saturation voltage	I _C = 1 A I _B = 0.2 A			1.2	V
h _{FE} ⁽¹⁾	DC current gain	$I_C = 10 \text{ mA}$ $V_{CE} = 5 \text{ N}$ $I_C = 1 \text{ A}$ $V_{CE} = 5 \text{ N}$ $I_C = 4 \text{ A}$ $V_{CE} = 5 \text{ N}$	/ 10	25	40	
V _F	Diode forward voltage	I _F = 2 A			2.5	V
t _s	Inductive load Storage time Fall time	$I_C = 2 \text{ A}$ $I_{B(on)} = 0.4$ $V_{BE(off)} = -5 \text{ V};$ $R_{BB(off)} = 0$ $V_{CC} = 200 \text{ V}$ $L = 200 \mu \text{H}$		0.6 0.1		μs ns

^{1.} Pulsed duration = 300 μ s, duty cycle \leq 1.5%.



ol

200

2.1 Electrical characteristics (curves)

Figure 2. Reverse biased safe operating area

| C | GIPG191120131118FSR | GIPG19112013118FSR | GIPG1911201318FSR | GIPG19112013118FSR | GIPG1911201318FSR | GIPG1911201318FSR | GIPG1911201318FSR | GIPG1911201318FSR | GIPG191918FSR | GIPG1918FSR | GIPG1918FSR

Figure 3. DC current gain

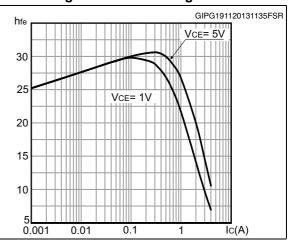


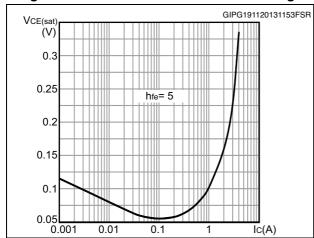
Figure 4. Collector-emitter saturation voltage

400

600

VCE(V)

Figure 5. Base-emitter saturation voltage



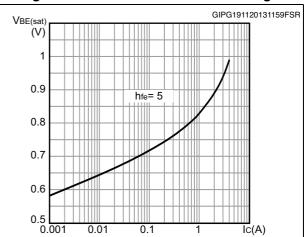
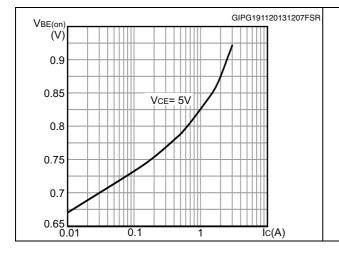
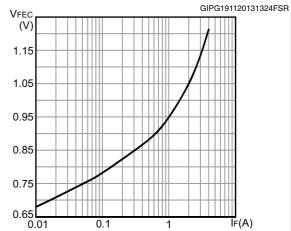


Figure 6. Base-emitter on-voltage

Figure 7. Diode forward voltage vs collector current

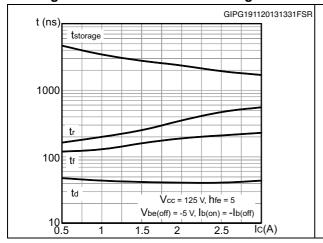


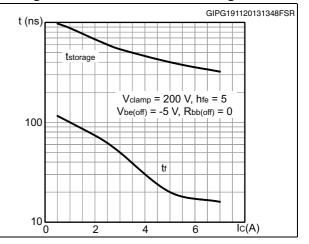


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Figure 8. Resistive load switching time

Figure 9. Inductive load switching time

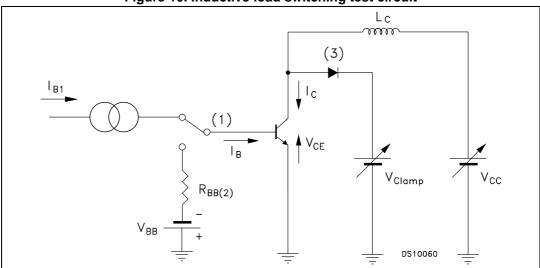




STD127DT4 Test circuits

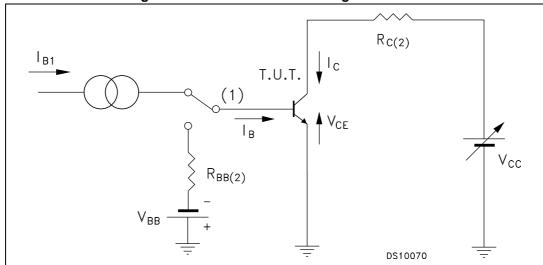
3 Test circuits

Figure 10. Inductive load switching test circuit



- 1. Fast electronic switch
- 2. Non-inductive resistor
- 3. Fast recovery rectifier

Figure 11. Resistive load switching test circuit



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 5. DPAK (TO-252) type C mechanical data

Di		mm	
Dim.	Min.	Тур.	Max.
А	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
С	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.25		
E	6.50	6.60	6.70
E1	4.70		
е	2.186	2.286	2.386
Н	9.80	10.10	10.40
L	1.40	1.50	1.70
L2	0.90		1.25
L4	0.60	0.80	1.00
Θ1	5°	7°	9°
Θ2	5°	7°	9°
V2	0°		8°

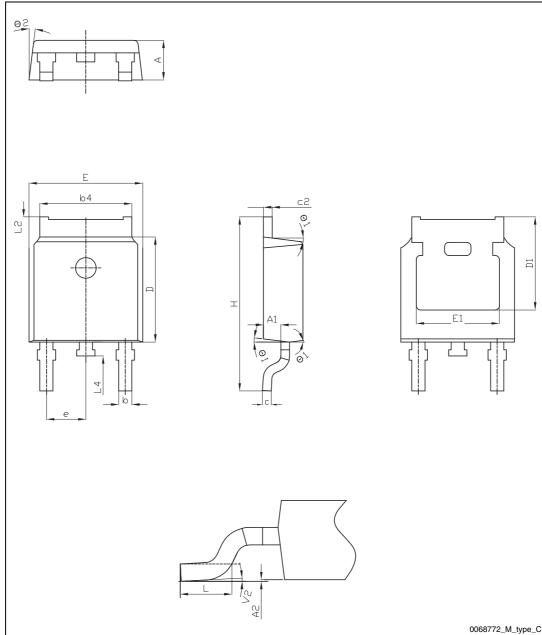


Figure 12. DPAK (TO-252) type C drawing

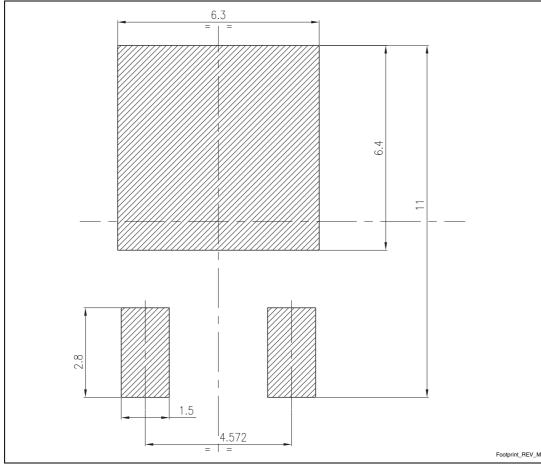


Figure 13. DPAK footprint (a)

a. All dimensions are in millimeters

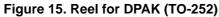
5 Packing mechanical data

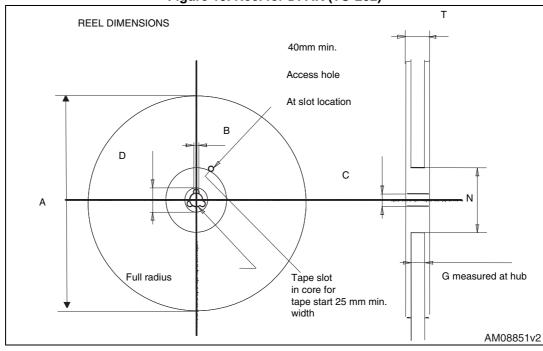
Table 6. DPAK (TO-252) tape and reel mechanical data

Tape				Reel	
Dim	mm		Dim.	mm	
Dim.	Min.	Max.	— Dim.	Min.	Max.
A0	6.8	7	А		330
В0	10.4	10.6	В	1.5	
B1		12.1	С	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
Е	1.65	1.85	N	50	
F	7.4	7.6	Т		22.4
K0	2.55	2.75			
P0	3.9	4.1		Base qty.	2500
P1	7.9	8.1		Bulk qty.	2500
P2	1.9	2.1			
R	40				
Т	0.25	0.35			
W	15.7	16.3			



Figure 14. Tape for DPAK (TO-252)





STD127DT4 Revision history

6 Revision history

Table 7. Document revision history

Date	Revision	Changes
19-Nov-2013	1	Initial release.

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